



Half-Bridge Driver

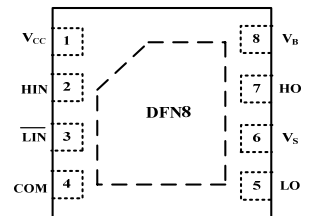
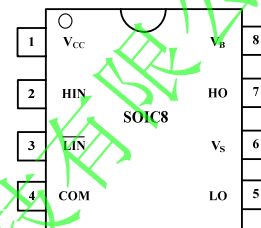
General Description

The PN7103 is a high voltage, high speed power MOSFET and IGBT driver based on P_SUB P_EPI process. The floating channel driver can be used to drive two N-channel power MOSFET or IGBT in a half-bridge configuration which operates up to 600 V. Logic inputs are compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. Propagation delays are matched to simplify use in high frequency applications.

Features

- Fully operational to +600 V
- 3.3 V logic compatible
- dV/dt Immunity ± 50 V/nsec
- Floating channel designed for bootstrap operation
- Gate drive supply range from 10 V to 20 V
- UVLO for low side channel
- Output Source / Sink Current Capability 300 mA / 600mA
- -5V negative V_s ability
- Matched propagation delay for both channels

Packages/Order information

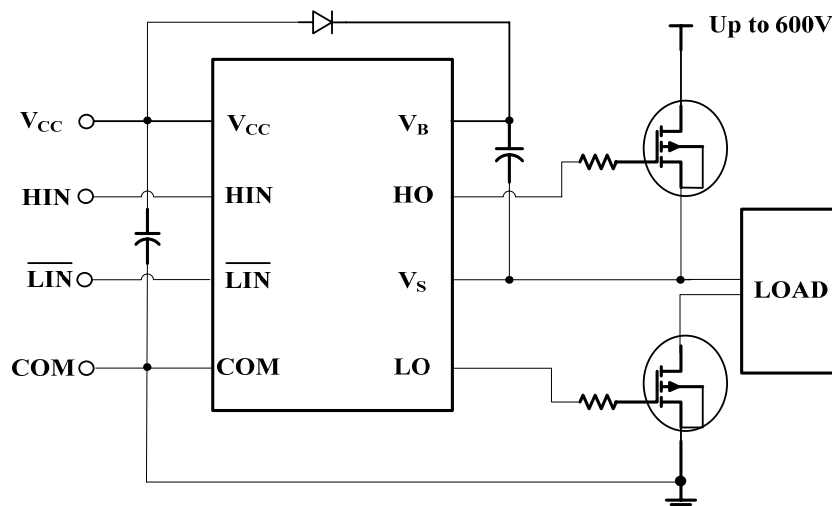


| Part number | Order Code | Package |
|-------------|--------------|---------|
| PN7103 | PN7103SEC-R1 | SOIC8 |
| PN7103 | PN7103DEC-R1 | DFN8 |

Applications

- Small and medium- power motor driver
- Power MOSFET or IGBT driver
- Half-Bridge Power Converters
- Full-Bridge Power Converters

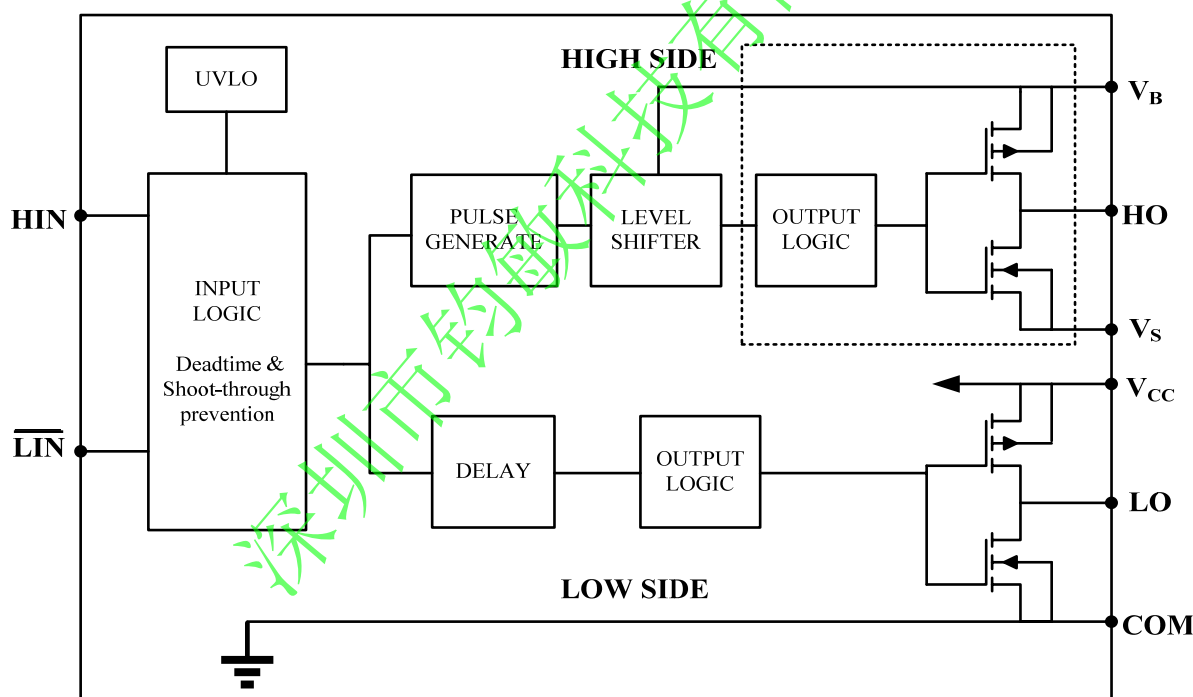
Typical Application Circuit



Pin Description

| PIN NO. | PIN NAME | PIN FUNCTION |
|---------|-------------------------|---|
| 1 | V _{CC} | Low side and main power supply |
| 2 | HIN | Logic input for high side gate driver output (HO) |
| 3 | $\overline{\text{LIN}}$ | Logic input for low side gate driver output (LO) |
| 4 | COM | Ground |
| 5 | LO | Low side gate drive output, out of phase with $\overline{\text{LIN}}$ |
| 6 | V _S | High side floating supply return or bootstrap return |
| 7 | HO | High side gate drive output, in phase with HIN |
| 8 | V _B | High side floating supply |

Functional Block Diagram



Absolute Maximum Ratings ^[Note1]

| Symbol | Definition | MIN. | MAX. | Units |
|---------------------|---|----------------------|-----------------------|-------|
| V _B | High side floating supply | -0.3 | 622 | V |
| V _S | High side floating supply return | V _B - 22 | V _B + 0.3 | |
| V _{HO} | High side gate drive output | V _S - 0.3 | V _B + 0.3 | |
| V _{CC} | Low side and main power supply | -0.3 | 22 | |
| V _{LO} | Low side gate drive output | -0.3 | V _{CC} + 0.3 | |
| V _{IN} | Logic input of HIN & LIN | -0.3 | V _{CC} + 0.3 | |
| dV _S /dt | Allowable Offset Supply Voltage Transient | -- | 50 | V/ns |
| ESD | HBM Model | 2.5 | | kV |
| | Machine Model | 200 | | V |
| P _D | Package Power Dissipation @ TA ≤ 25°C | 8 Lead SOIC | 0.625 | W |
| RthJA | Thermal Resistance Junction to Ambient | 8 Lead SOIC | 200 | °C/W |
| T _J | Junction Temperature | -- | 150 | °C |
| T _S | Storage Temperature | -55 | 150 | |
| T _L | Lead Temperature (Soldering, 10 seconds) | -- | 300 | |

Note 1: Exceeding these ratings may damage the device.

Recommended Operating Conditions

| Symbol | Definition | MIN. | MAX. | Units |
|-----------------|-------------------------------------|---------------------|---------------------|-------|
| V _B | High side floating supply | V _S + 10 | V _S + 20 | V |
| V _S | High side floating supply return | - | 600 | |
| V _{HO} | High side gate drive output voltage | V _S | V _B | |
| V _{CC} | Low side supply | 10 | 20 | |
| V _{LO} | Low side gate drive output voltage | 0 | V _{CC} | |
| V _{IN} | Logic input voltage(HIN & LIN) | 0 | V _{CC} | |
| T _A | Ambient temperature | -40 | 125 | °C |

Dynamic Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}) = 15V, C_L = 1000 pF and T_A = 25°C unless otherwise specified.

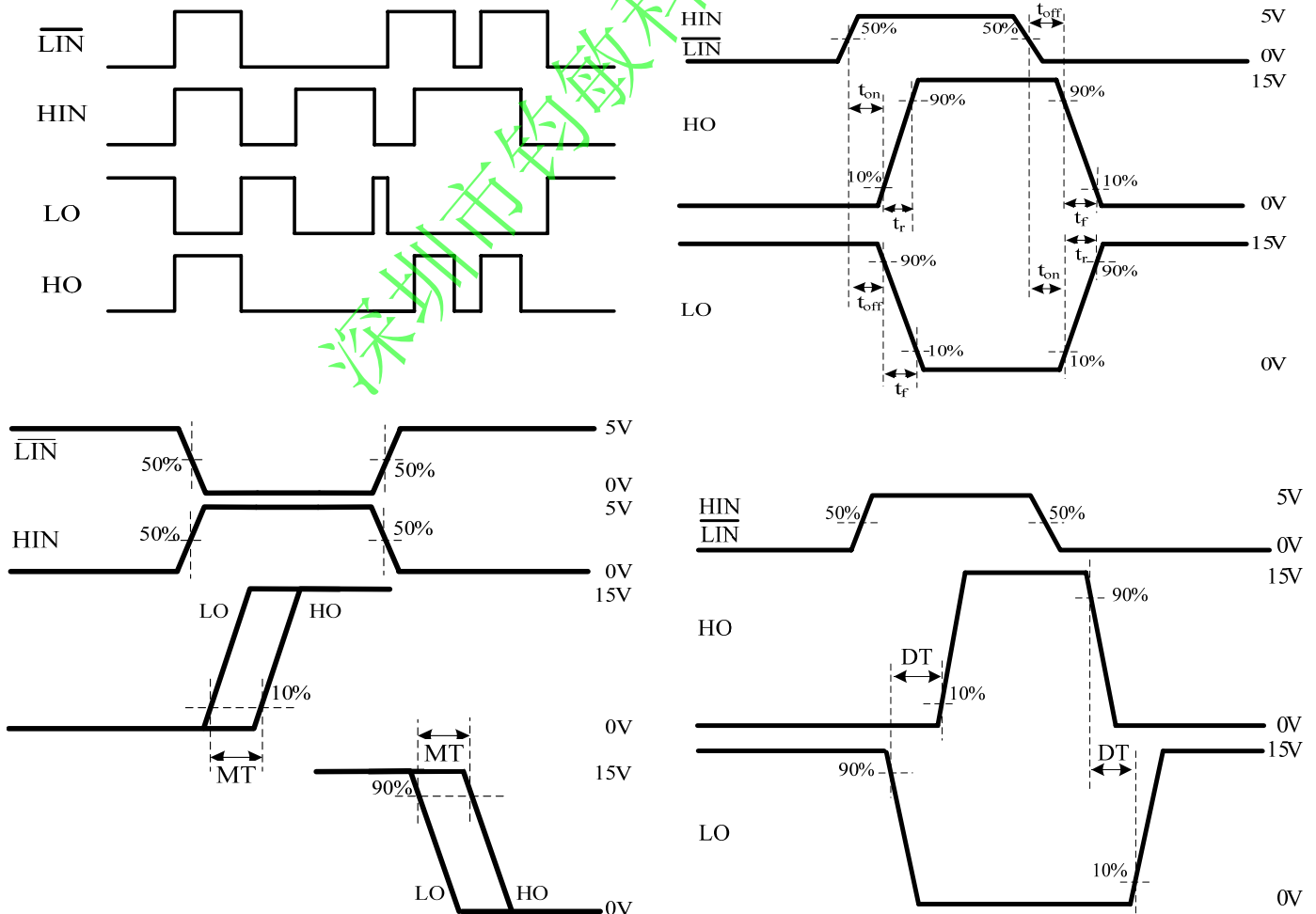
| Symbol | Definition | TYP. | MAX. | Units |
|-------------------|--------------------------------------|------|------|-------|
| t _{onH} | High side turn-on propagation delay | 630 | 820 | ns |
| t _{offH} | High side turn-off propagation delay | 140 | 220 | |
| t _{onL} | Low side turn-on propagation delay | 630 | 820 | |
| t _{offL} | Low side turn-off propagation delay | 140 | 220 | |
| MT | Delay matching | - | 50 | |
| DT | Dead time | 500 | 650 | |
| t _r | Turn-on rise time | 85 | 120 | |
| t _f | Turn-off fall time | 35 | 90 | |

Static Electrical Characteristics

$V_{BIAS} (V_{CC}, V_{BS}) = 15V, C_L = 1000 \text{ pF}$ and $T_A = 25^\circ\text{C}$ unless otherwise specified.

| Symbol | Definition | MIN. | TYP. | MAX. | Units |
|------------|--|------|------|------|---------------|
| V_{IH} | Logic "1"(HIN) & Logic "0"($\overline{\text{LIN}}$) input voltage | 2.5 | - | - | V |
| V_{IL} | Logic "0" (HIN)& Logic "1"($\overline{\text{LIN}}$) input voltage | - | - | 0.8 | |
| V_{OH} | High level output voltage, $V_{BIAS} - V_O$ | - | - | 0.1 | |
| V_{OL} | Low level output voltage, V_O | - | - | 0.1 | |
| I_{QCC} | Quiescent V_{CC} supply current | - | 150 | 270 | μA |
| I_{QBS} | Quiescent V_B supply current | - | 30 | 55 | |
| I_{LK} | Leakage current from $V_S(600V)$ to GND | - | - | 10 | |
| I_{IN+} | Logic "1" input bias current (HIN "1" & $\overline{\text{LIN}}$ "0") | - | 6 | 20 | |
| I_{IN-} | Logic "0" input bias current (HIN "0" & $\overline{\text{LIN}}$ "1") | - | - | 15 | V |
| V_{CCU+} | V_{CC} supply UVLO threshold | - | 8.7 | - | |
| V_{CCU-} | | - | 8 | - | |
| I_{O+} | Output high short circuit pulsed current | - | 300 | -- | mA |
| I_{O-} | Output low short circuit pulsed current | - | 600 | -- | |

Logic Function & Timing Spec



Characterization Curves

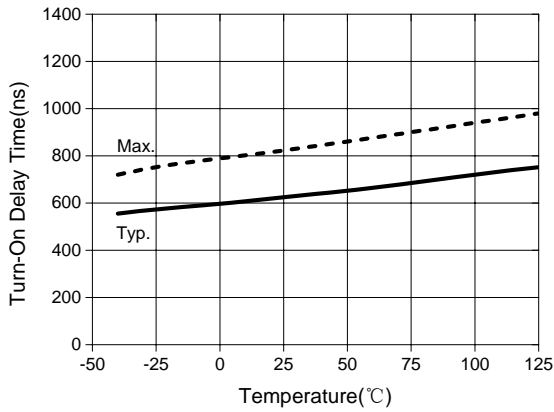


Fig.1 Turn-On Delay vs. Temperature

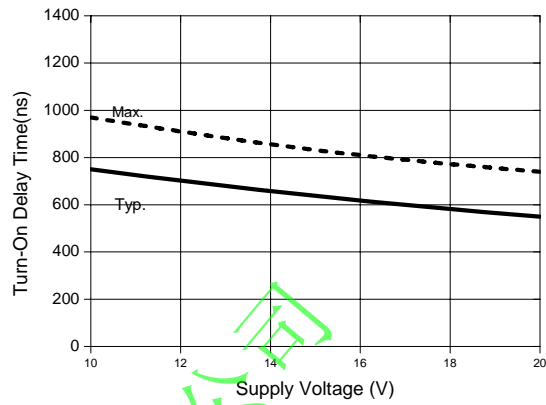


Fig.2 Turn-On Delay vs. Supply Voltage

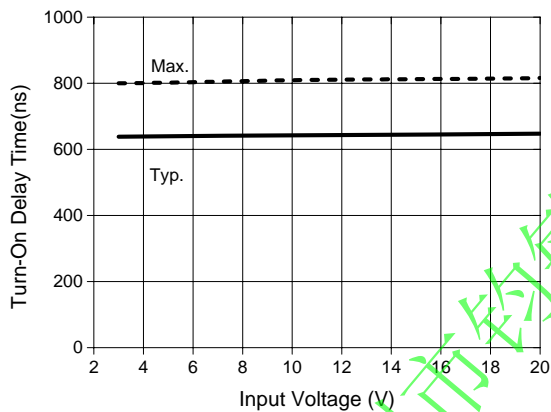


Fig.3 Turn-On Delay Time vs. Input Voltage

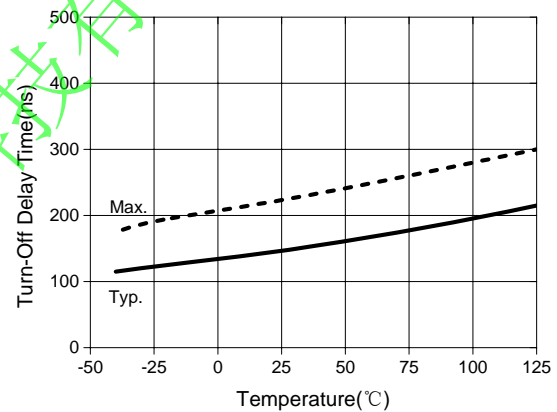


Fig.4 Turn-Off Delay Time vs. Temperature

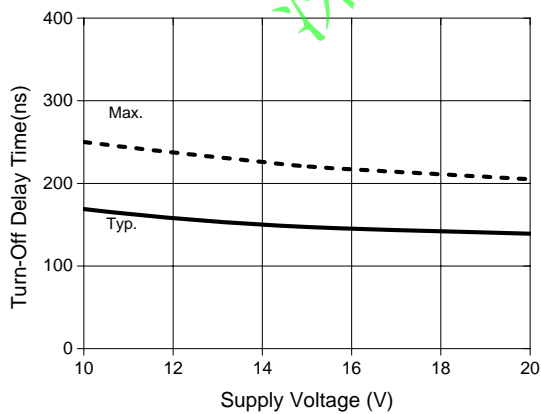


Fig.5 Turn-Off Delay Time vs. Supply Voltage

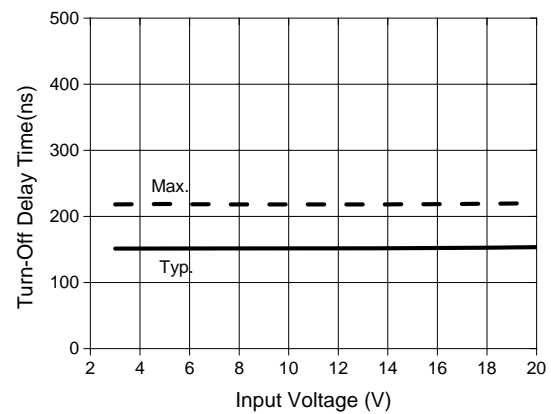


Fig.6 Turn-Off Delay Time vs. Input Voltage

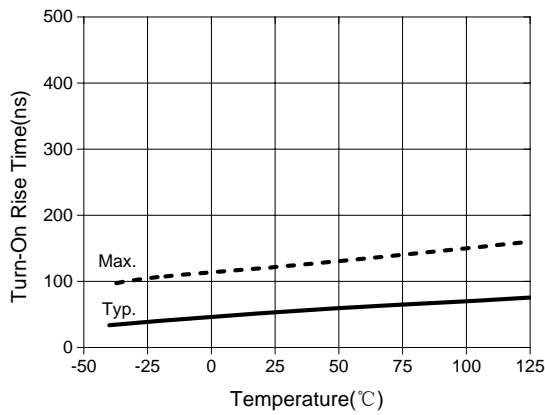


Fig.7 Turn-On Rise Time vs. Temperature

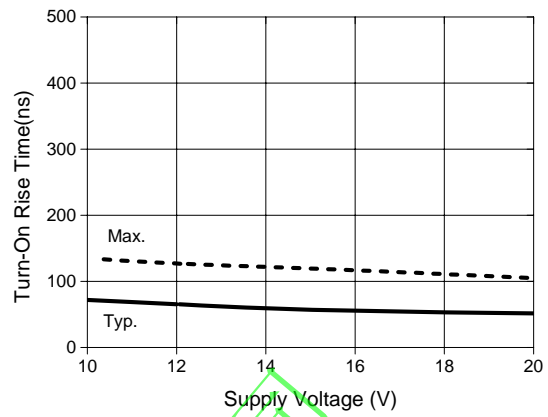


Fig.8 Turn-On Rise Time vs. Supply Voltage

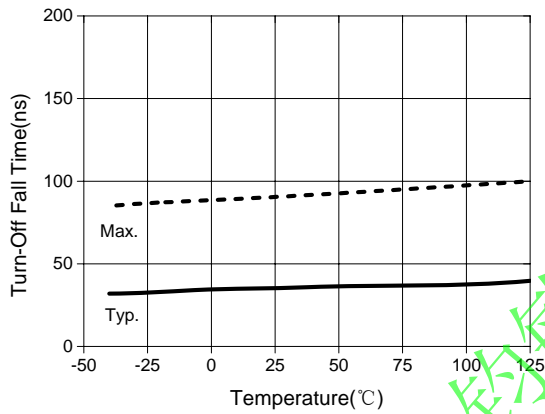


Fig.9 Turn-Off Fall Time vs. Temperature

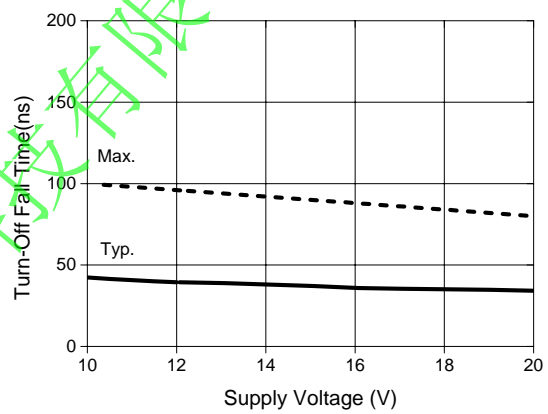


Fig.10 Turn-Off Fall Time vs. Supply Voltage

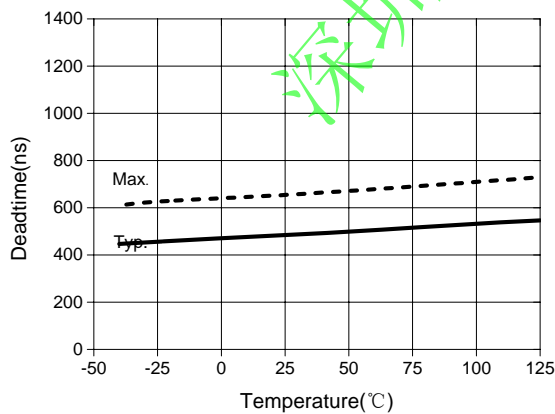


Fig.11 Dead time vs. Temperature

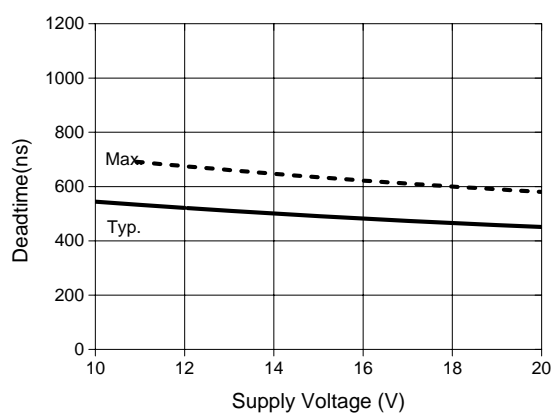


Fig.12 Dead time vs. Supply Voltage

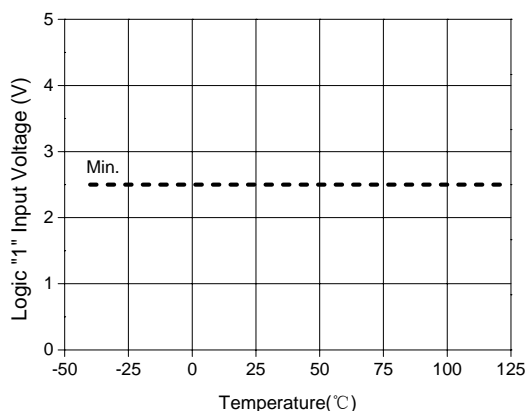


Fig.13 Logic "1" Input Voltage vs. Temperature

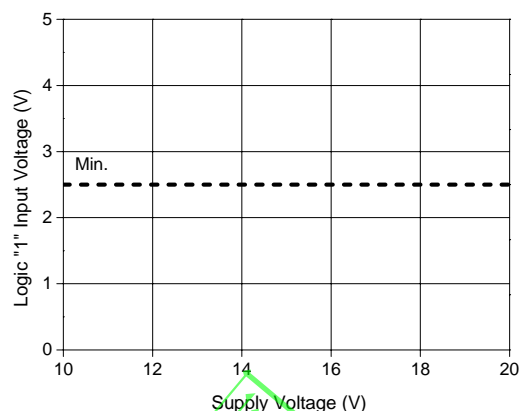


Fig.14 Logic "1" Input Voltage vs. Supply Voltage

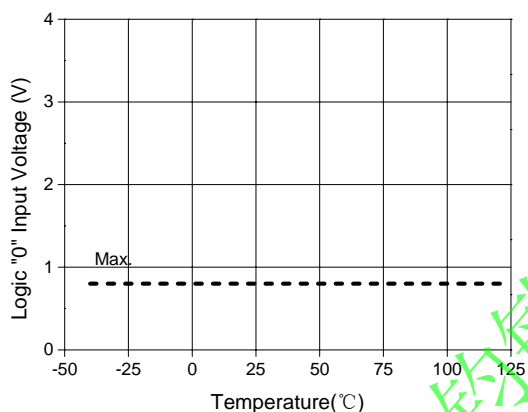


Fig.15 Logic "0" Input Voltage vs. Temperature

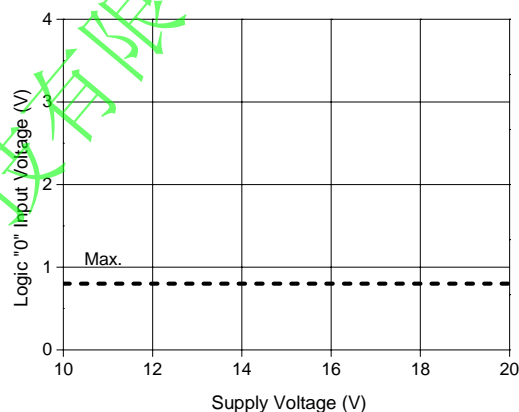


Fig.16 Logic "0" Input Voltage vs. Supply Voltage

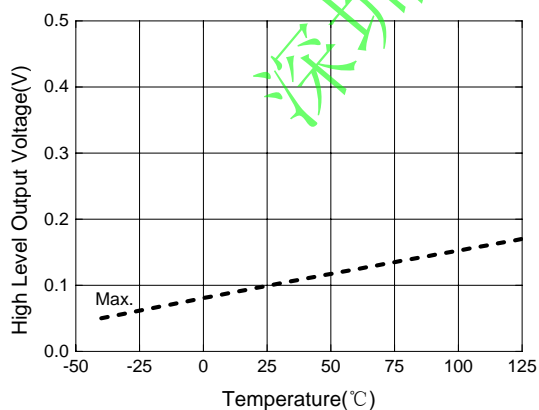


Fig.17 High Level Output vs. Temperature

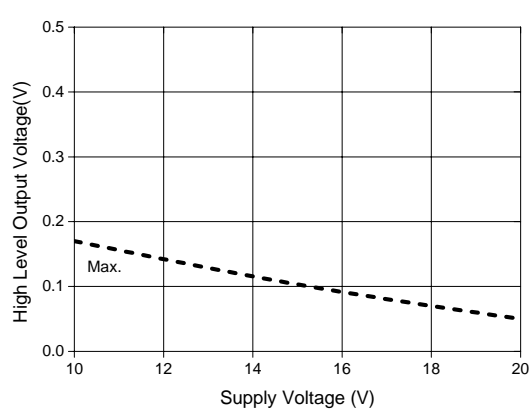


Fig.18 High Level Output vs. Supply Voltage

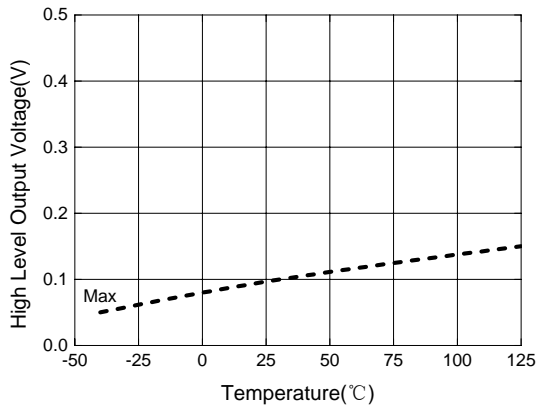


Fig.19 Low Level Output vs. Temperature

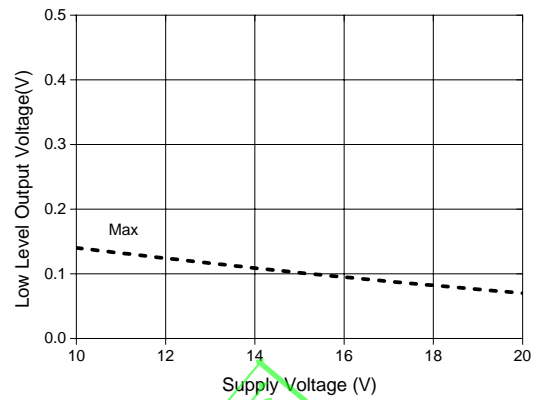


Fig.20 Low Level Output vs. Supply Voltage

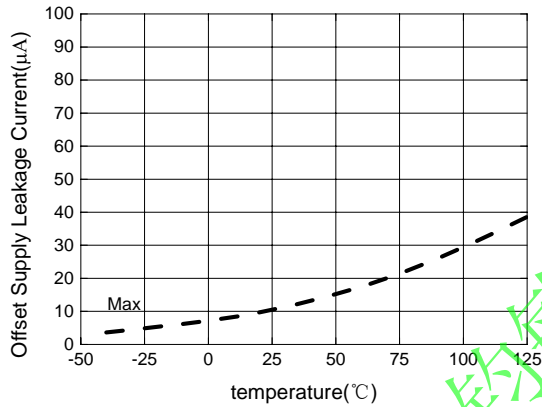


Fig.21 Offset Supply Current vs. Temperature

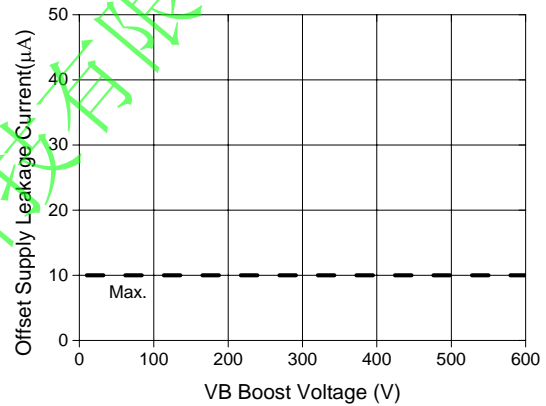


Fig.22 Offset Supply Current vs. Boost Voltage

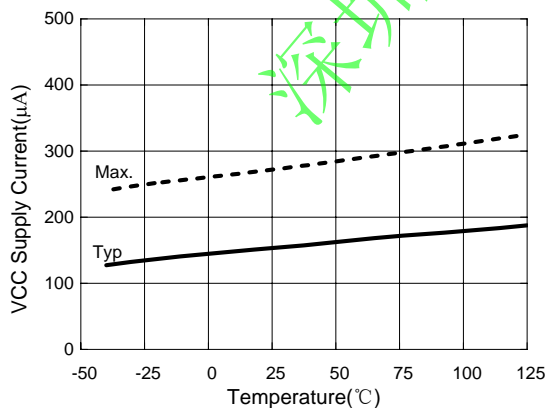


Fig.23 VCC Supply Current vs. Temperature

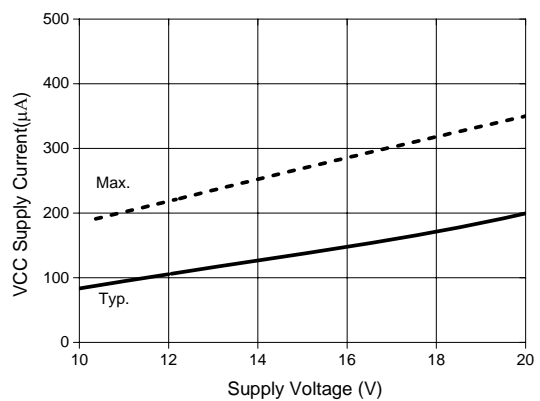


Fig.24 VCC Supply Current vs. Supply Voltage

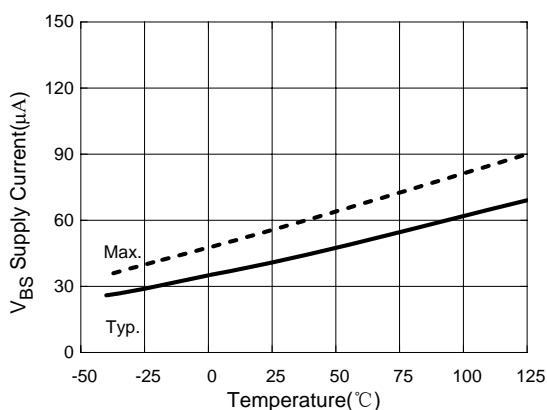


Fig.25 VBS Supply Current vs. Temperature

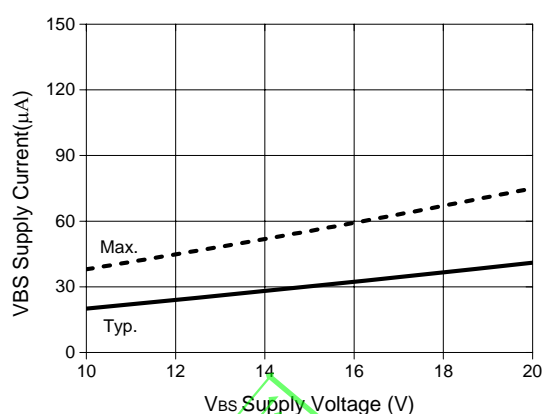


Fig.26 VBS Supply Current vs. Supply Voltage

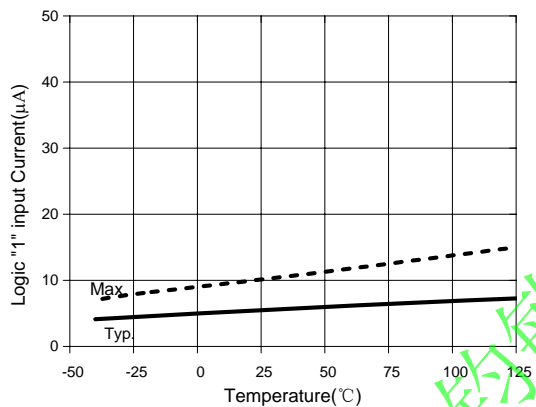


Fig.27 Logic "1" Input Current vs. Temperature

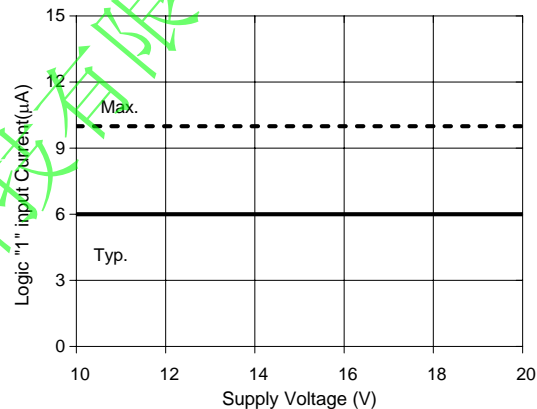


Fig.28 Logic "1" Input Current vs. Supply Voltage

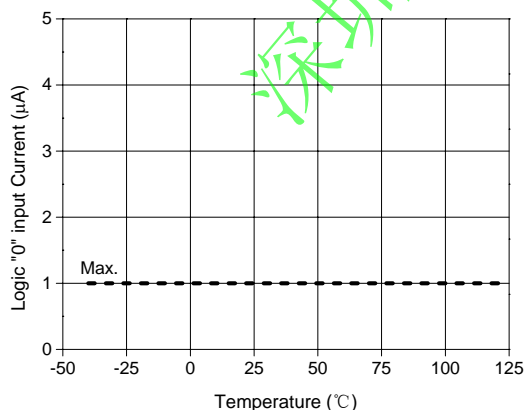


Fig.29 Logic "0" Input Current vs. Temperature

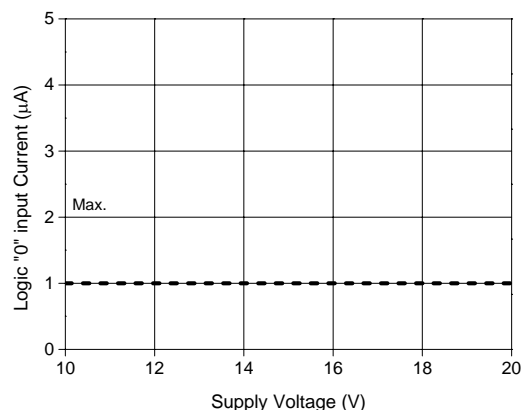
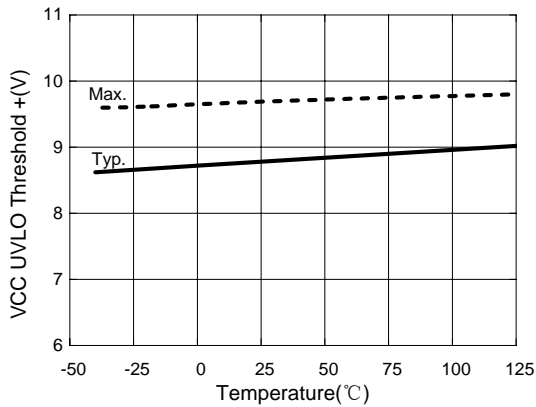
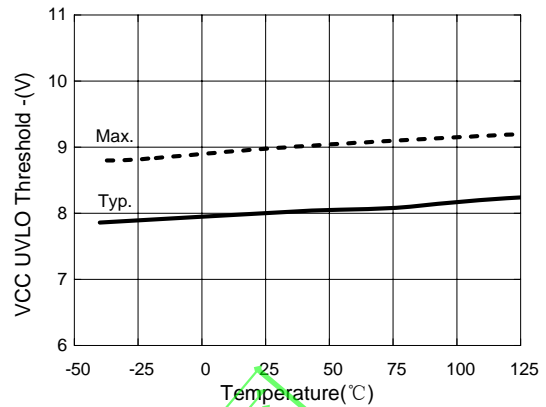


Fig.30 Logic "0" Input Current vs. Supply Voltage



**Fig.31 VCC Under voltage Threshold(+)
vs. Temperature**



**Fig.32 VCC Under voltage Threshold(-)
vs. Temperature**

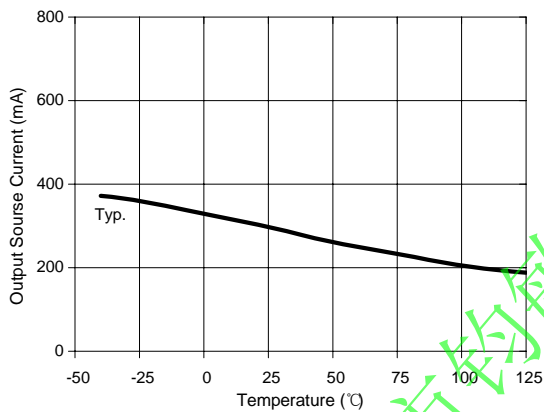


Fig.33 Output Source Current vs. Temperature

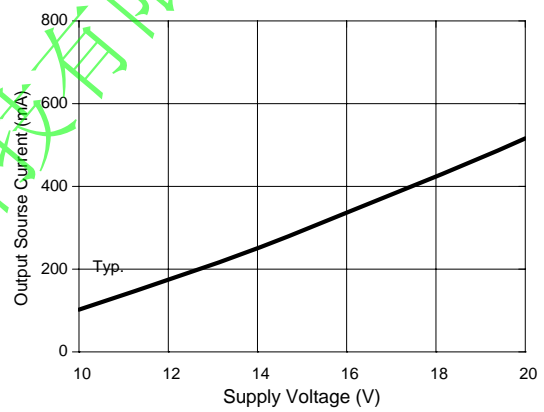
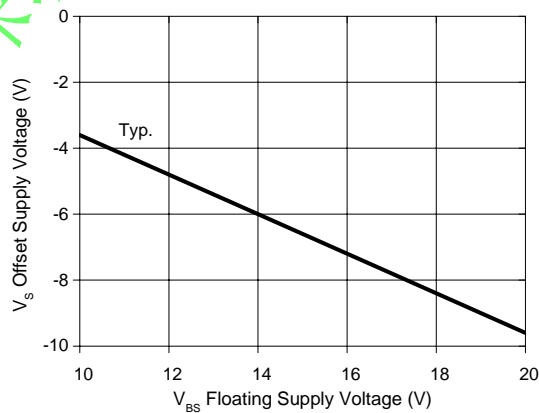


Fig.34 Output Source Current vs. Supply Voltage



**Fig.35 Maximum V_S Negative Offset
vs. Supply Voltage**

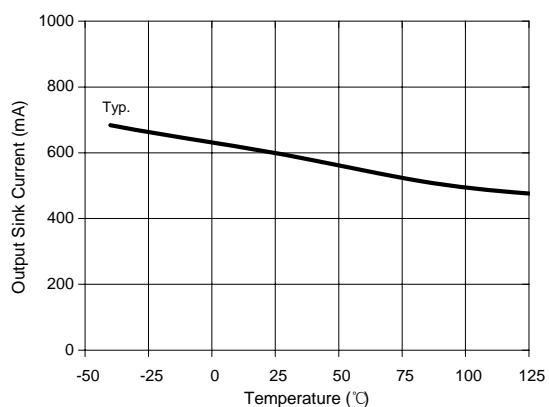


Fig.36 Output Sink Current vs. Temperature

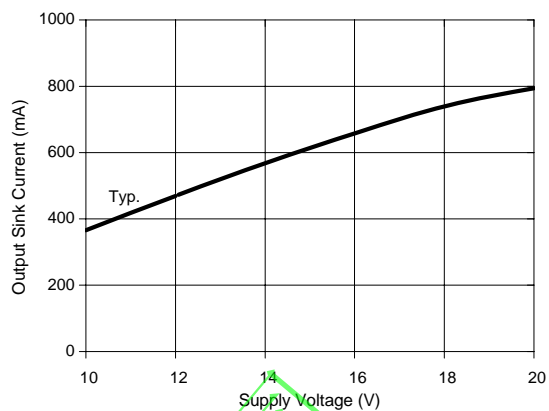


Fig.37 Output Sink Current vs. Supply Voltage

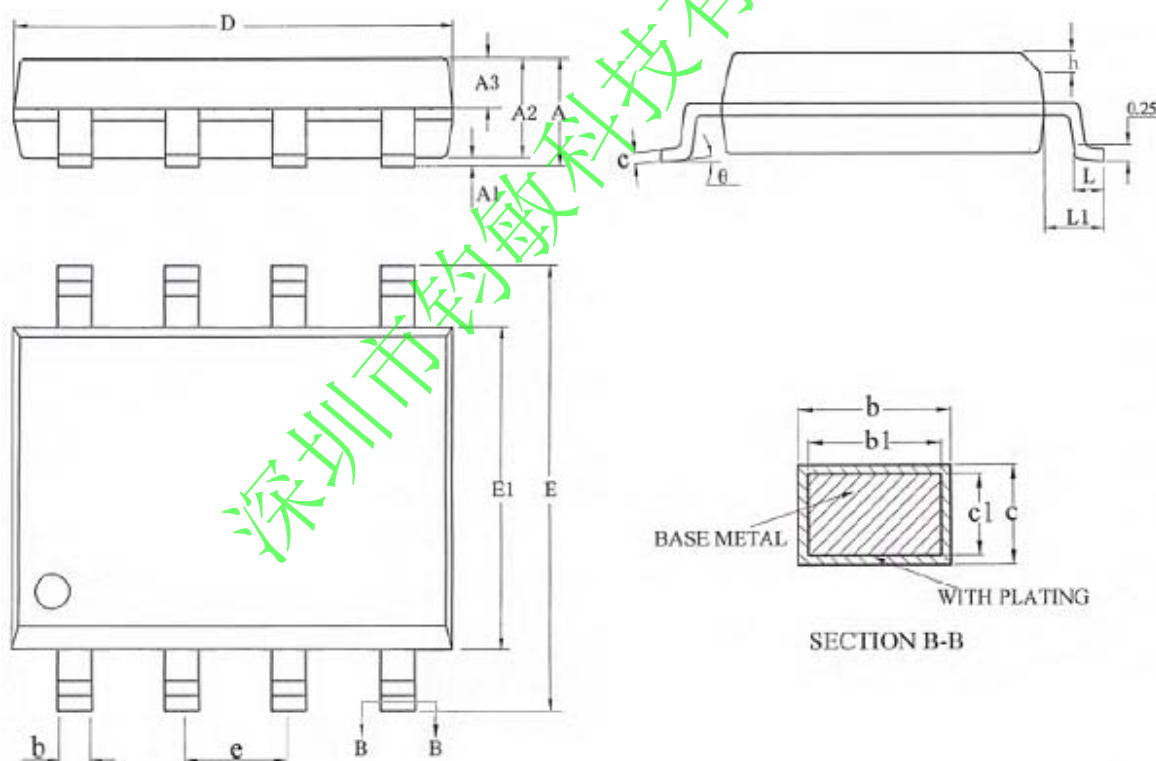
深圳市钧敏科技有限公司

Package Information

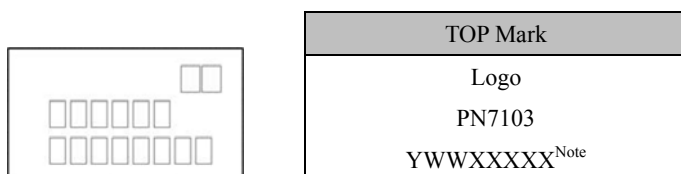
SOIC8 Package Dimensions

| Size Symbol | MIN(mm) | TYP(mm) | MAX(mm) | Size Symbol | MIN(mm) | TYP(mm) | MAX(mm) |
|----------------|---------|---------|---------|----------------|---------|---------|---------|
| A | - | - | 1.75 | D | 4.70 | 4.90 | 5.10 |
| A1 | 0.10 | - | 0.225 | E | 5.80 | 6.00 | 6.20 |
| A2 | 1.30 | 1.40 | 1.50 | E1 | 3.70 | 3.90 | 4.10 |
| A3 | 0.60 | 0.65 | 0.70 | e | 1.27BSC | | |
| b | 0.39 | - | 0.48 | h | 0.25 | - | 0.50 |
| b1 | 0.38 | 0.41 | 0.43 | L | 0.50 | - | 0.80 |
| c | 0.21 | - | 0.26 | L1 | 1.05BSC | | |
| c1 | 0.19 | 0.20 | 0.21 | θ | 0 | - | 8° |

Package Outlines



SOIC8 Package Mark Information

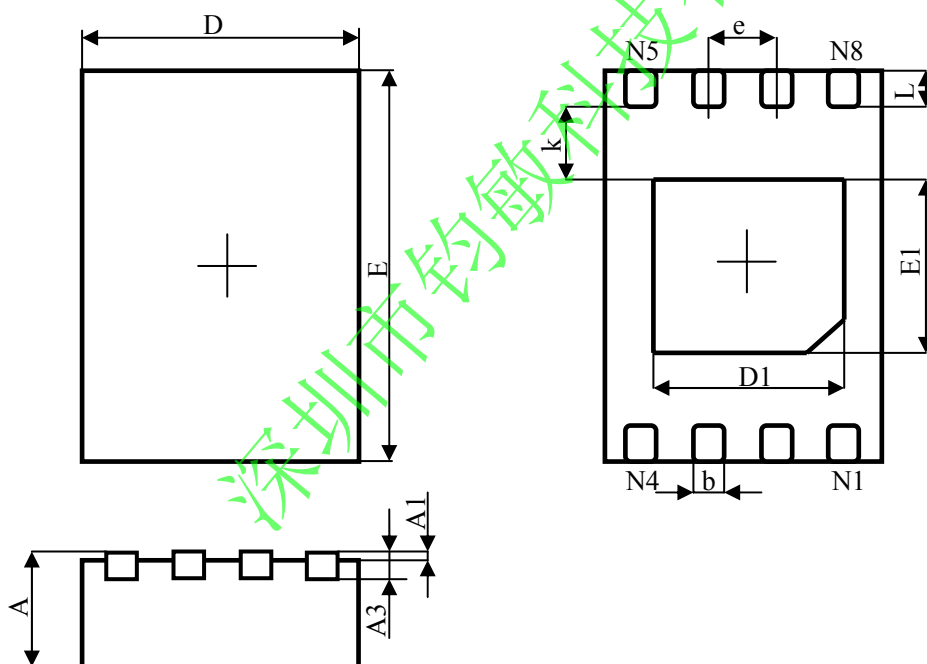


Note: Y: Year code, WW: Week codes, XXXXX: Package codes

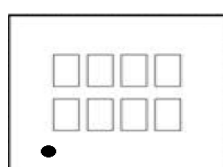
DFN8 Package Dimensions

| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------------|----------------------|-------------|
| | Min. | Max. | Min. | Max. |
| A | 0.700/0.800 | 0.800/0.900 | 0.028/0.031 | 0.031/0.035 |
| A1 | 0.000 | 0.050 | 0.000 | 0.002 |
| A3 | 0.203REF. | | 0.008REF. | |
| D | 1.924 | 2.076 | 0.076 | 0.082 |
| E | 2.924 | 3.076 | 0.115 | 0.121 |
| D1 | 1.400 | 1.600 | 0.055 | 0.063 |
| E1 | 1.400 | 1.600 | 0.055 | 0.063 |
| k | 0.200MIN. | | 0.008MIN. | |
| b | 0.200 | 0.300 | 0.008 | 0.012 |
| e | 0.500TYP. | | 0.020TYP. | |
| L | 0.224 | 0.376 | 0.009 | 0.015 |

Package Outlines



DFN8 Package Mark Information



| TOP Mark |
|-----------------------|
| 7103 |
| AYWX ^{Note} |
| Pin 1 indicator point |

Note: A: Internal code, Y: Year code, W: Week codes, X: Package codes



Mosway Technologies Ltd.

PN7103

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